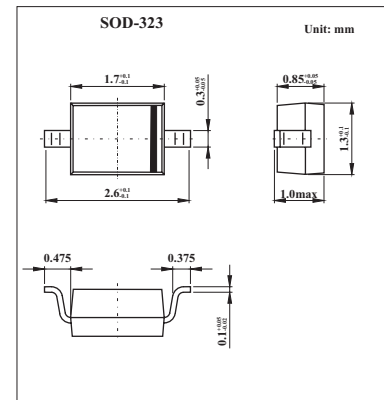


High-Speed Diode

KAS316(BAS316)

■ Features

- Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
repetitive peak reverse voltage	VRRM	85	V
continuous reverse voltage	VR	75	V
continuous forward current	IF	250	mA
repetitive peak forward current	IFRM	500	mA
non-repetitive peak forward current	IFSM	4	A
t = 1 ms		1	A
t = 1 μs		0.5	A
power dissipation	PD	400	mW
junction temperature	Tj	150	°C
storage temperature	Tstg	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Forward voltage	VF	IF = 1 mA			715	mV
		IF = 10 mA			855	mV
		IF = 50 mA			1	v
		IF = 150 mA			1.25	v
Leakage current	IR	VR = 25 V			30	nA
		VR = 75 V			1	μA
		VR = 25 V; Tj = 150 °C			30	μA
		VR = 75 V; Tj = 150 °C			50	μA
Junction Capacitance	CJ	VR = 0, f = 1.0MHz			1.5	pF
reverse recovery time	trr	when switched from IF = 10 mA to IR = 10mA; RL = 100 Ω; measured at IR = 1 mA			4	ns

■ Marking

Marking	A6
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